INTEGRATED CIRCUITS

DATA SHEET



74F00Quad 2-input NAND gate

Product specification

1990 Oct 04

IC15 Data Handbook





Quad 2-input NAND gate

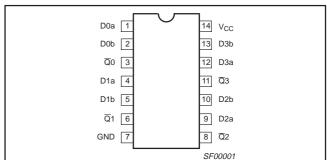
74F00

FEATURE

• Industrial temperature range available (-40°C to +85°C)

TYPE	TYPICAL PROPAGATION DELAY	TYPICAL SUPPLY CURRENT (TOTAL)
74F00	3.4ns	4.4mA

PIN CONFIGURATION



ORDERING INFORMATION

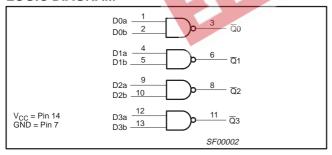
	C	PRDER CODE	
DESCRIPTION		INDUSTRIAL RANGE V_{CC} = 5V ±10%, T_{amb} = -40°C to +85°C	PKG DWG #
14-pin plastic DIP	N74F00N	174F00N	SOT27-1
14-pin plastic SO	N74F00D	I74F00D	SOT108-1

INPUT AND OUTPUT LOADING AND FAN OUT TABLE

PINS	DESCRIPTION	74F (U.L.) HIGH/LOW	LOAD VALUE HIGH/LOW
Dna, Dnb	Data inputs	1.0/1.0	20μA/0.6mA
Qn	Data output	50/33	1.0mA/20mA

NOTE: One (1.0) FAST unit load is defined as: 20µA in the high state and 0.6mA in the low state.

LOGIC DIAGRAM



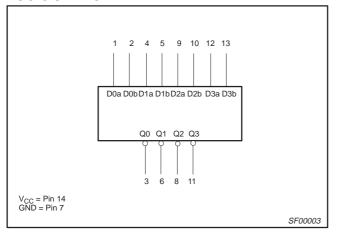
FUNCTION TABLE

INP	UTS	OUTPUT
Dna	Dnb	Ūn
L	L	Н
L	Н	Н
Н	L	Н
Н	Н	L

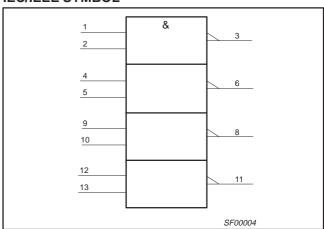
NOTES:

H = High voltage level L = Low voltage level

LOGIC SYMBOL



IEC/IEEE SYMBOL



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ABSOLUTE MAXIMUM RATINGS

(Operation beyond the limit set forth in this table may impair the useful life of the device. Unless otherwise noted these limits are over the operating free air temperature range.)

SYMBOL	PARAMETER		RATING	UNIT
V _{CC}	Supply voltage		−0.5 to +7.0	V
V _{IN}	Input voltage		-0.5 to +7.0	V
I _{IN}	Input current		−30 to +5	mA
V _{OUT}	Voltage applied to output in high output state		−0.5 to V _{CC}	V
l _{OUT}	Current applied to output in low output state		40	mA
T _{amb}	Operating free air temperature range	Commercial range	0 to +70	°C
		Industrial range	-40 to +85	°C
T _{stg}	Storage temperature range	-65 to +150	°C	

RECOMMENDED OPERATING CONDITIONS

SYMBOL	PARAMETER			LIMITS							
			25c	MIN	NOM	MAX	1				
V _{CC}	Supply voltage		2 13	4.5	5.0	5.5	V				
V _{IH}	High-level input voltage		33	2.0			V				
V _{IL}	Low-level input voltage		60			0.8	V				
I _{lk}	Input clamp current	1				-18	mA				
I _{OH}	High-level output current					-1	mA				
l _{OL}	Low-level output current					20	mA				
T _{amb}	Operating free air temperature range	Comi	nercial range	0		+70	°C				
		Indu	ıstrial range	-40		+85	°C				

DC ELECTRICAL CHARACTERISTICS

(Over recommended operating free-air temperature range unless otherwise noted.)

SYMBOL	PARAMETER		TEST CONDITIO	NS ¹		LIMITS		UNIT	
					MIN	TYP ²	MAX		
V _{OH}	High-level output voltage		$V_{CC} = MIN, V_{IL} = MAX$	±10%V _{CC}	2.5			V	
			$V_{IH} = MIN, I_{OH} = MAX$ $\pm 5\% V_{CC}$		2.7	3.4		V	
V _{OL}	Low-level output voltage		$V_{CC} = MIN, V_{IL} = MAX$	±10%V _{CC}		0.30	0.50	V	
			$V_{IH} = MIN, I_{OI} = MAX$		0.30	0.50	V		
V _{IK}	Input clamp voltage		$V_{CC} = MIN, I_I = I_{IK}$			-0.73	-1.2	V	
II	Input current at maximum voltage	input	$V_{CC} = MAX, V_I = 7.0V$				100	μΑ	
I _{IH}	High-level input current		$V_{CC} = MAX, V_I = 2.7V$				20	μΑ	
I _{IL}	Low-level input current		$V_{CC} = MAX, V_I = 0.5V$				-0.6	mA	
Ios	Short-circuit output currer	nt ³	$V_{CC} = MAX$		-60		-150	mA	
Icc	Supply current (total)	I _{CCH}	$V_{CC} = MAX$ $V_{IN} = GND$			1.9	2.8	mA	
		I _{CCL}	$V_{CC} = MAX$	V _{IN} = 4.5V		6.8	10.2	mA	

- 1. For conditions shown as MIN or MAX, use the appropriate value specified under recommended operating conditions for the applicable type.
- All typical values are at V_{CC} = 5V, T_{amb} = 25°C.
 Not more than one output should be shorted at a time. For testing I_{OS}, the use of high-speed test apparatus and/or sample-and-hold techniques are preferable in order to minimize internal heating and more accurately reflect operational values. Otherwise, prolonged shorting of a high output may raise the chip temperature well above normal and thereby cause invalid readings in other parameter tests. In any sequence of parameter tests, I_{OS} tests should be performed last.

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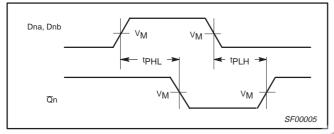
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AC ELECTRICAL CHARACTERISTICS

	PARAMETER					LIM	ITS			
SYMBOL		TEST CONDITION	Tai	_{CC} = +5.0 _{mb} = +25 0pF, R _L =	°C	T _{amb} = 0°0	0V ± 10% C to +70°C R _L = 500Ω	$V_{CC} = +5.$ $T_{amb} = -40^{\circ}$ $C_{L} = 50 pF$,	UNIT	
			MIN	TYP	MAX	MIN	MAX	MIN	MAX	
t _{PLH}	Propagation delay Dna, Dnb to Qn	Waveform 1	2.4 2.0	3.7 3.2	5.0 4.3	2.4 2.0	6.0 5.3	2.0 1.5	6.5 6.0	ns

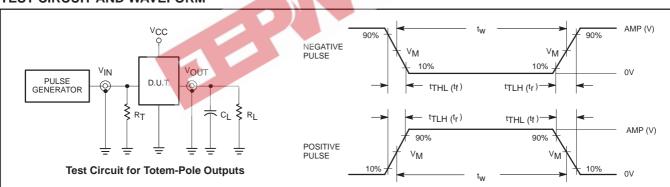
AC WAVEFORMS

For all waveforms, $V_M = 1.5V$.



Waveform 1. Propagation delay for inverting outputs

TEST CIRCUIT AND WAVEFORM



DEFINITIONS:

R_L = Load resistor;

see AC ELECTRICAL CHARACTERISTICS for value.

CL = Load capacitance includes jig and probe capacitance; see AC ELECTRICAL CHARACTERISTICS for value.

 $R_T = \mbox{Termination resistance should be equal to Z_{OUT} of pulse generators.}$

Input Pulse Definition

family	INP	INPUT PULSE REQUIREMENTS											
	amplitude	V_{M}	rep. rate	t _w	t _{THL}								
74F	3.0V 1.5V		1MHz	500ns	2.5ns	2.5ns							

SF00006

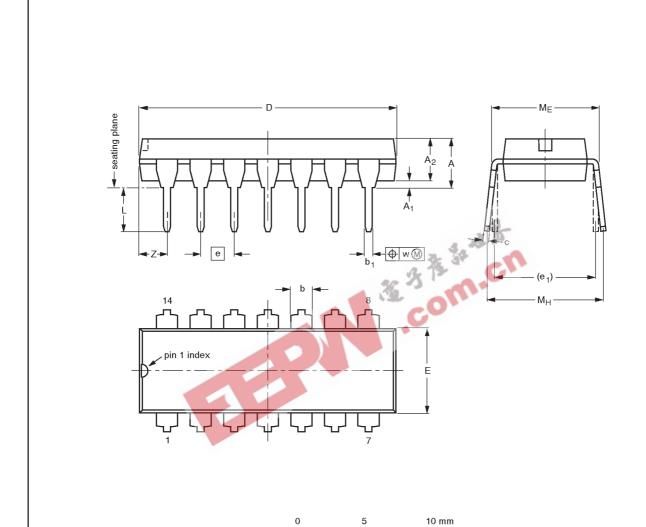
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DIP14: plastic dual in-line package; 14 leads (300 mil)

SOT27-1



scale

DIMENSIONS (inch dimensions are derived from the original mm dimensions)

UNIT	A max.	A ₁ min.	A ₂ max.	b	b ₁	С	D ⁽¹⁾	E ⁽¹⁾	е	e ₁	L	ME	M _H	w	Z ⁽¹⁾ max.
mm	4.2	0.51	3.2	1.73 1.13	0.53 0.38	0.36 0.23	19.50 18.55	6.48 6.20	2.54	7.62	3.60 3.05	8.25 7.80	10.0 8.3	0.254	2.2
inches	0.17	0.020	0.13	0.068 0.044	0.021 0.015	0.014 0.009	0.77 0.73	0.26 0.24	0.10	0.30	0.14 0.12	0.32 0.31	0.39 0.33	0.01	0.087

Note

1. Plastic or metal protrusions of 0.25 mm maximum per side are not included.

OUTLINE		REFER	EUROPEAN	ISSUE DATE			
VERSION	IEC	JEDEC	EIAJ		PROJECTION	ISSOL DATE	
SOT27-1	050G04	MO-001AA				92-11-17 95-03-11	

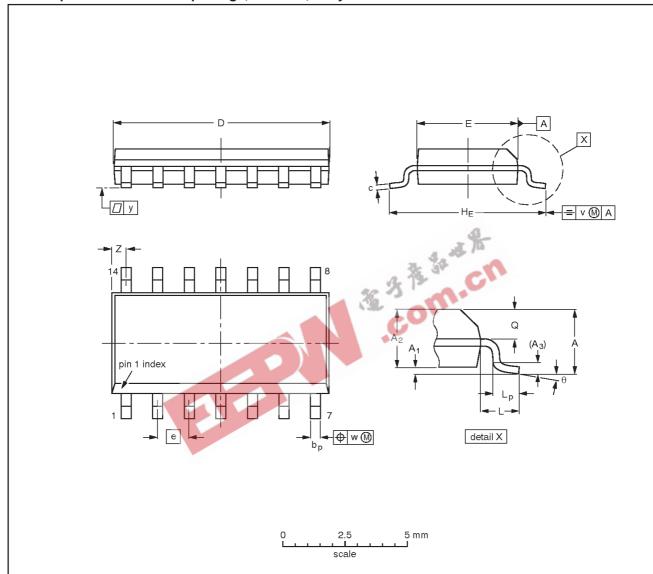
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SO14: plastic small outline package; 14 leads; body width 3.9 mm

SOT108-1



DIMENSIONS (inch dimensions are derived from the original mm dimensions)

UNIT	A max.	A ₁	A ₂	А3	bp	С	D ⁽¹⁾	E ⁽¹⁾	е	HE	L	Lp	Q	v	w	у	Z ⁽¹⁾	θ
mm	1.75	0.25 0.10	1.45 1.25	0.25	0.49 0.36	0.25 0.19	8.75 8.55	4.0 3.8	1.27	6.2 5.8	1.05	1.0 0.4	0.7 0.6	0.25	0.25	0.1	0.7 0.3	8°
inches	0.069	0.010 0.004	0.057 0.049	0.01		0.0100 0.0075	0.35 0.34	0.16 0.15	0.050	0.244 0.228	0.041	0.039 0.016	0.028 0.024	0.01	0.01	0.004	0.028 0.012	0°

Note

1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.

OUTLINE	REFERENCES				EUROPEAN	ISSUE DATE
VERSION	IEC	JEDEC	EIAJ		PROJECTION	ISSUE DATE
SOT108-1	076E06S	MS-012AB				95-01-23 97-05-22

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NOTES



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Data sheet status

Data sheet status	Product status	Definition [1]	
Objective specification	Development	This data sheet contains the design target or goal specifications for product development. Specification may change in any manner without notice.	
Preliminary specification	Qualification	This data sheet contains preliminary data, and supplementary data will be published at a later date. Philips Semiconductors reserves the right to make chages at any time without notice in order to improve design and supply the best possible product.	
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^[1] Please consult the most recently issued datasheet before initiating or completing a design.

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Limiting values definition — Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

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